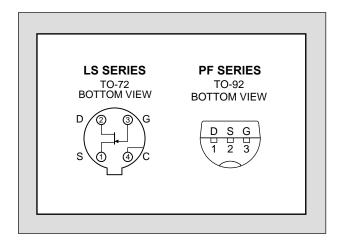


Linear Integrated Systems

FEATURES				
DIRECT REPLACEMENT FOR LF5301, PF5301, & 2N5301				
HIGH INPUT INPEDANCE	$I_G = 0.100 \text{ pA}$			
HIGH GAIN	g _{fs} = 70 μS			
ABSOLUTE MAXIMUM RATINGS ¹				
@ 25 °C (unless otherwise stated)				
Maximum Temperatures				
Storage Temperature (TO-72)	-65 to 175°C			
Storage Temperature (TO-92)	-65 to 150°C			
Maximum Power Dissipation				
Continuous Power Dissipation	300mW			
Maximum Currents				
Gate Current	50mA			
Maximum Voltages				
Gate to Drain	-30V			
Gate to Source	-30V			

LS5301, PF5301

VERY HIGH INPUT IMPEDANCE N-CHANNEL JFET



COMMON ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNIT	CONDITIONS
BV_GSS	Gate to Source Breakdown Voltage	-30			V	$V_{DS} = 0V$, $I_D = -1\mu A$
$V_{GS(off)}$	Gate to Source Cutoff Voltage	0.6		3.0]	$V_{DS} = 10V, I_{D} = 1nA$
I _{GSS}	Gate Leakage Current			-1	nΛ	V_{DS} = 0V, V_{GS} = -15V
I _G	Gate Operating Current		0.04		pА	$V_{DG} = 6V, I_{D} = 5\mu A$
I _{DSS}	Drain to Source Saturation Current	30		500	μA	V_{DS} = 10V, V_{GS} = 0V
g fs	Forward Transconductance	70		300	μS	$V_{DS} = 10V, V_{GS} = 0V, f = 1kHz$
C _{iss}	Input Capacitance			3	nE	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$
C _{rss}	Reverse Transfer Capacitance			1.5	pF	V _{DS} = 10V, V _{GS} = 0V, I = 11VII 12
en	Equivalent Noise Voltage		45	150	nV/√Hz	$V_{DG} = 10V$, $I_D = 50\mu A$, $f = 100Hz$

NOTES

1. Absolute maximum ratings are limiting values above which serviceability may be impaired.

Information furnished by Linear Integrated Systems is believed to be accurate and reliable. However, no responsibility is assumed for its use; nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Linear Integrated Systems.

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.